

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	0	chakravarth near srinivasan.in.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM - TDB	2004/02/2 0 11:51	
2	BRS	L2	109	chidambaram.in.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM - TDB	2004/02/2 0 11:53	
3	BRS	L3	128	438/369.cc1s.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM - TDB	2004/02/2 0 11:54	
4	BRS	L4	31	2 and (wafer or substrate)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM - TDB	2004/02/2 0 11:56	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
5	BRS	L5	148	pre-amorphize or preamorphiz\$3 or pre near amorphiz\$3	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM _TDB	2004/02/2 0 11:57	
6	BRS	L6	72	(pre-amorphize or preamorphiz\$3 or pre near amorphiz\$3) near30 (wafer or substrate)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM _TDB	2004/02/2 0 11:57	
7	BRS	L7	40	(pre-amorphize or preamorphiz\$3 or pre near amorphiz\$3) near30 (wafer or substrate) near25 (implant\$3)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM _TDB	2004/02/2 0 12:28	
8	BRS	L8	5244	(energy) near30 (wafer or substrate) near25 (implant\$3)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM _TDB	2004/02/2 0 12:28	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
9	BRS	L9	6	(energy) near30 (pre-amorphiz\$3) near25 (wafer or substrate) near25 (implant\$3)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/02/2 0 12:29	
10	BRS	L10	50	(energy) near30 (amorphiz\$3) near25 (wafer or substrate) near25 (implant\$3)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/02/2 0 12:46	
11	BRS	L11	288940	(coat\$3 or boron) near15 (wafer or substrate)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/02/2 0 12:47	
12	BRS	L12	9208	(coat\$3 or boron) near15 (dop\$3) near15 (wafer or substrate)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/02/2 0 12:47	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	261	(coat\$3 or boron) near15 (dop\$3) near15 (wafer or substrate) near15 (anneal\$3)	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/02/2 0 12:48	
14	BRS	L14	2	(coat\$3 or boron) near15 (target near dop\$3) near15 (wafer or substrate) near15 (anneal\$3)	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/02/2 0 12:47	
15	BRS	L15	87	(coat\$3 or boron) near15 (dop\$3) near15 (wafer or substrate) near15 (anneal\$3) near15 (diffus\$3)	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/02/2 0 12:48	

	U	1	Document ID	Title	Current OR	Pages	Issue Date
1	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20030085730 A1	Apparatus and method for evaluating a wafer of semiconductor material	324/765	52	20030508
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20030013260 A1	Increasing the electrical activation of ion-implanted dopants	438/301	8	20030116
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20020187614 A1	Methods for forming ultrashallow junctions with low sheet resistance	438/407	11	20021212
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6632728 B2	Increasing the electrical activation of ion-implanted dopants	438/527	8	20031014
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6489801 B1	Apparatus and method for evaluating a semiconductor wafer	324/766	47	20021203
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6049220 A	Apparatus and method for evaluating a wafer of semiconductor material	324/765	50	20000411